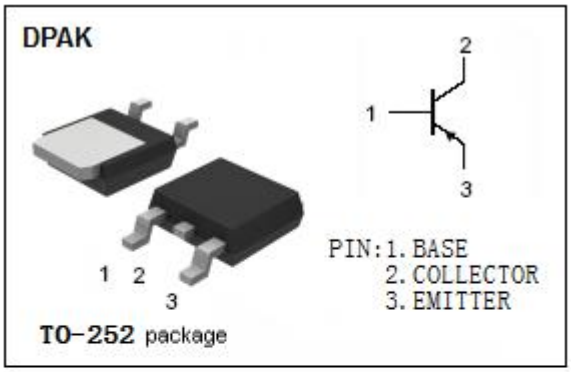
isc Silicon PNP Power Transistor STD888



DESCRIPTION

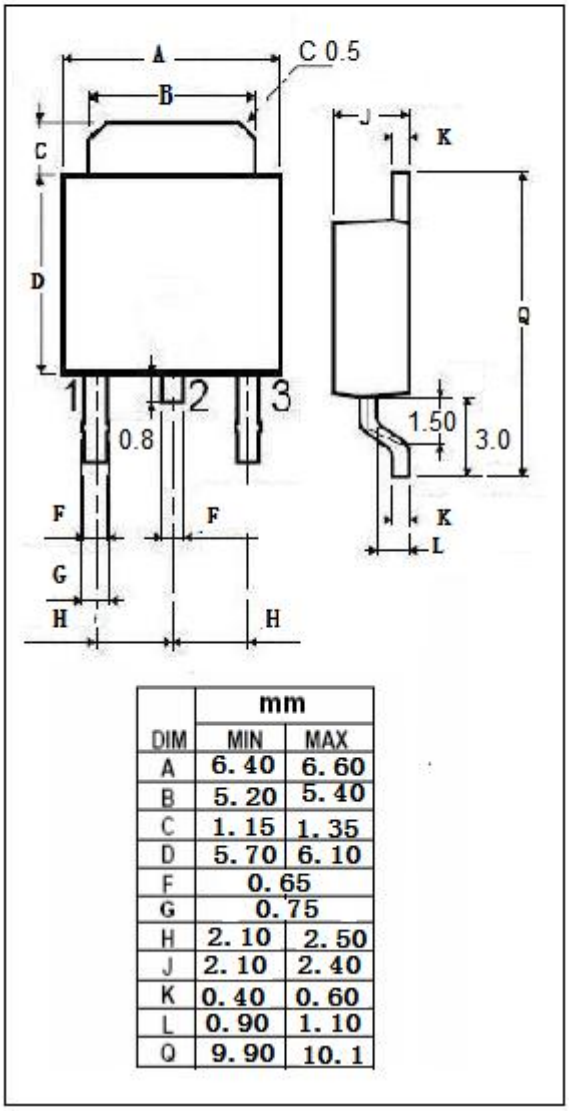
- Low Collector-Emitter Saturation Voltage-
  : $V_{CE(sat)}$= -0.7V(Max)(I_C= -5A; I_B= -0.25A)
- DC Current Gain -h_{FE} = 150(Min)@ I_C= -0.5A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Power amplifier applications
- Voltage regulation in bias supply circuits applications
- Switching regulator inbattery charger applications

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-5	A
I_{CM}	Collector Current-Peak	-10	A
P_C	Total Power Dissipation @ T_C=25℃	15	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃



DIM	mm MIN	MAX
A	6.40	6.60
B	5.20	5.40
C	1.15	1.35
D	5.70	6.10
F	0.65	
G	0.75	
H	2.10	2.50
J	2.10	2.40
K	0.40	0.60
L	0.90	1.10
Q	9.90	10.1

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E=-0.1mA,I_C=0	-6			V
$V_{(BR)CEO}$ *	Collector-Emitter Breakdown Voltage	I_C=-10mA, I_B=0	-30			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C=-0.1mA ,I_E=0	-60			V
$V_{CE(sat)}$ *	Collector-Emitter Saturation Voltage	I_C= -0.5A; I_B= -5mA			-0.15	V
		I_C= -2A; I_B= -50mA			-0.25	V
		I_C= -5A; I_B= -0.25A			-0.7	V
		I_C= -6A; I_B= -0.25A			-0.7	V
		I_C= -8A; I_B= -0.4A			-1.0	V
		I_C= -10A; I_B= -0.5A			-1.5	V
$V_{BE(sat)}$*	Base-Emitter Saturation Voltage	I_C= -2A; I_B= -50mA			-1.1	V
		I_C= -6A; I_B= -0.25A			-1.4	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -30V; I_E= 0			-10	nA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -6V; I_C=0			-10	nA
h_{FE}*	DC Current Gain	I_C= -10mA; V_{CE}= -1V	150			
		I_C= -0.5A; V_{CE}= -1V	150		300	
		I_C= -5A; V_{CE}= -1V	75			

* Pulse Test: PW≤300μs, Duty Cycle≤1.5%

Switching Times; Resistive Load

t_d	Delay Time	I_C= -3A; V_{CC}= 20V; I_{B1}= I_{B2}= -60mA			220	ns
t_r	Rise Time				210	ns
t_s	Storage Time				300	ns
t_f	Fall Time				100	ns

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